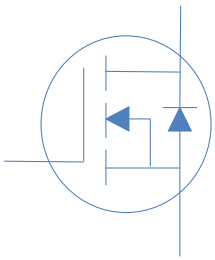
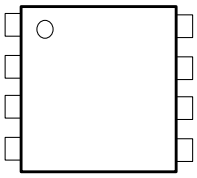
120V N-Ch Power MOSFET

DS(on),typ			Ω
DS(on),typ			Ω





=25 (unless otherwise specified)

		=25		
		=100		
		=25		
Avalanche Energy, Single Pulse	E	=25		
Power Dissipation		=25		W
Operating and Storage Temperature				

Thermal Resistance Junction-Ambient	θ		/W
Thermal Resistance Junction-Case	θ		/W

8

Ω

f

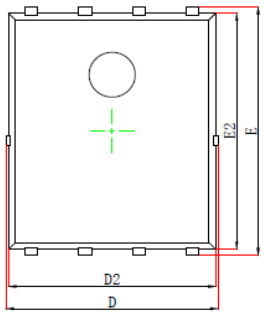
Reverse Diode Characteristics

Fig 1. Typical Output Characteristics	

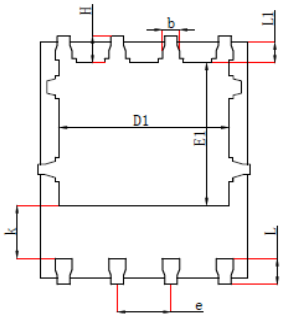
	Figure 4. Normalized On-Resistance vs. Junction Temperature

Figure 5. Typical Transfer Characteristics	Figure 6. Typical Source-Drain Diode Forward Voltage

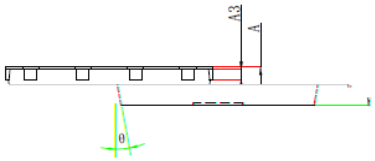
DFN5x6_P, 8 Leads



Top View
[顶视图]



Bottom View
[背视图]



Side View
[侧视图]

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.100	0.035	0.043
A3	0.254 REF		0.010REF	
D	4.680	5.120	0.184	0.202
E	[illegible]	[illegible]	[illegible]	[illegible]
D1	3.610	4.110	0.142	0.162
E1	3.380	3.780	0.133	0.149
D2	4.800	5.000	0.189	0.197
E2	5.674	5.826	0.223	0.229
k	1.100	1.390	0.043	0.055
b	0.330	0.510	0.013	0.020
e	1.270TYP		1.270TYP	
L	0.510	0.711	0.020	0.028
[illegible]	0.017	0.023	L1	0.424	0.576
[illegible]	0.029	[illegible]	[illegible]	0.726	0.016
[illegible]	[illegible]	[illegible]	θ	[illegible]	[illegible]